

Title (en)
REMOVAL OF HIGH-DOSE ION-IMPLANTED PHOTORESIST USING SELF-ASSEMBLED MONOLAYERS IN SOLVENT SYSTEMS

Title (de)
ENTFERNEN VON HOCHIONENDOTIERTEM PHOTOLACK MIT SELBSTORGANISIERTEN MONOSCHICHTEN IN
LÖSUNGSMITTELSYSTEMEN

Title (fr)
ELIMINATION DE PHOTORESINE A IMPLANTATION IONIQUE HAUTE DOSE AU MOYEN DE MONOCOUCHEES AUTO-ASSEMBLEES DANS
DES SYSTEMES DE SOLVANTS

Publication
EP 1877530 A2 20080116 (EN)

Application
EP 06749725 A 20060410

Priority
• US 2006013430 W 20060410
• US 67185105 P 20050415

Abstract (en)
[origin: WO2006113222A2] A method and self assembled monolayer (SAM)-containing compositions for removing bulk and hardened photoresist material from microelectronic devices have been developed. The SAM-containing composition includes at least one solvent, at least one catalyst, at least one SAM component, and optionally a surfactant. The SAM-containing compositions effectively remove the hardened photoresist material while simultaneously passivating the underlying silicon-containing layer(s) in a one step process.

IPC 8 full level
H01L 21/311 (2006.01); **B82Y 30/00** (2011.01); **C11D 3/16** (2006.01); **C11D 3/28** (2006.01); **C11D 3/30** (2006.01); **C11D 3/43** (2006.01); **C11D 7/22** (2006.01); **C11D 7/32** (2006.01); **C11D 7/50** (2006.01); **C11D 11/00** (2006.01); **G03F 7/42** (2006.01)

CPC (source: EP KR)
B82Y 30/00 (2013.01 - EP); **C11D 3/162** (2013.01 - EP); **C11D 3/28** (2013.01 - EP); **C11D 3/30** (2013.01 - EP); **C11D 3/43** (2013.01 - EP); **C11D 7/22** (2013.01 - EP); **C11D 7/3209** (2013.01 - EP); **C11D 7/5004** (2013.01 - EP); **G03F 7/422** (2013.01 - EP); **G03F 7/425** (2013.01 - EP); **H01L 21/228** (2013.01 - KR); **H01L 21/31133** (2013.01 - EP); **C11D 2111/22** (2024.01 - EP); **H01L 21/266** (2013.01 - EP)

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DOCDB simple family (publication)
WO 2006113222 A2 20061026; WO 2006113222 A3 20071108; CN 101198683 A 20080611; CN 101198683 B 20110914;
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DOCDB simple family (application)
US 2006013430 W 20060410; CN 200680021622 A 20060410; EP 06749725 A 20060410; JP 2008506595 A 20060410;
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